

Docket No. 740756-2297

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: )  
Shunpei YAMAZAKI et al. ) Group Art Unit: 2814  
Serial No. 09/837,558 ) Examiner: Ngan V. Ngo  
Filed: April 19, 2001 )  
For: SEMICONDUCTOR DEVICE AND ) Date: September 20, 2002  
MANUFACTURING METHOD THEREOF )

## RESPONSE TO RESTRICTION REQUIREMENT AND AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Official Action of August 26, 2002, Applicants respond as follows:

**IN THE CLAIMS:**

Please cancel claims 17-30 without prejudice or disclaimer to file a divisional application directed thereto.

Please add new claims 33-50 as follows:

- 33. A method of manufacturing a semiconductor device comprising:
- forming a conductive film over a substrate;
  - patterning said conductive film to form at least one first wiring, said first wiring including at least one first gate electrode;
  - forming a first insulating film over said first wiring and said substrate;
  - forming a first semiconductor island and a second semiconductor island wherein said first semiconductor island is located over said first gate electrode with said first insulating film

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